

### KSP10

### **VHF/UHF** transistor



1. Base 2. Emitter 3. Collector

### **NPN Epitaxial Silicon Transistor**

### Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
$V_{EBO}$	Emitter-Base Voltage	3.0	V
P <sub>C</sub>	Collector Dissipation (T <sub>a</sub> =25°C)	350	mW
	Derate above 25°C	2.8	mW/°C
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	1.0	W
	Derate above 25°C	8.0	W/°C
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55~150	°C
Rth(j-c)	Thermal Resistance, Junction to Case	125	°C/W
Rth(j-a)	Thermal Resistance, Junction to Ambient	357	°C/W

# **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =100μA, I <sub>E</sub> =0	30		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =1mA, I <sub>B</sub> =0	25		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	3.0		V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =25V, $I_{E}$ =0		100	nA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =2V, I <sub>C</sub> =0		100	nA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA	60		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =4mA, I <sub>B</sub> =0.4mA		0.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA		0.95	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =4mA, f=100MHz	650		MHz
	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		0.7	pF
C <sub>ob</sub>	Collector Base Feedback Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	0.35	0.65	pF
C <sub>c·rbb′</sub>	Collector Base Time Constant	V <sub>CB</sub> =10V, I <sub>C</sub> =4mA, f=31.8MHz		9.0	ps

<sup>\*</sup> Pulse Test: PW≤300µs, Duty Cycle≤2%

## **Typical Characteristics**

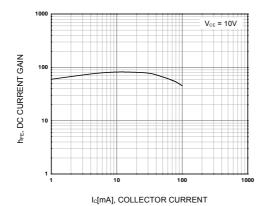


Figure 1. DC current Gain

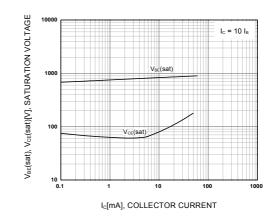


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

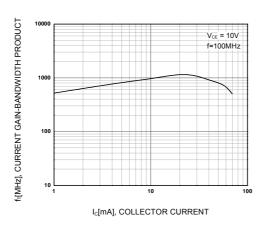


Figure 3. Current Gain Bandwidth Product

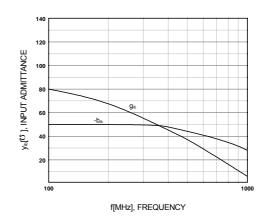


Figure 4. Rectangular Form

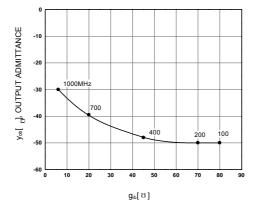


Figure 5. Polar Form

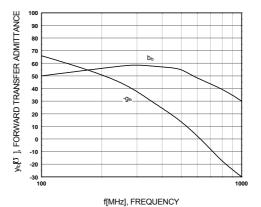


Figure 6. Rectangular Form

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## **Typical Characteristics** (Continued)

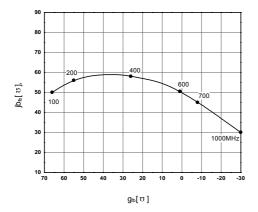


Figure 7. Polar Form

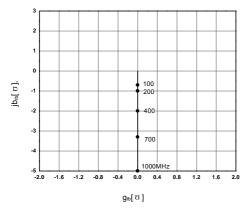


Figure 9. Polar Form

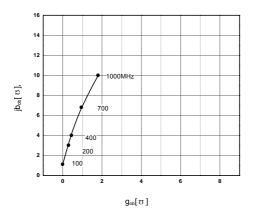


Figure 11. Polar Form

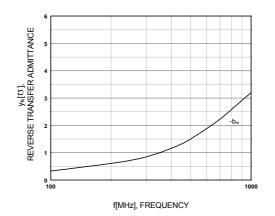


Figure 8. Rectangular Form

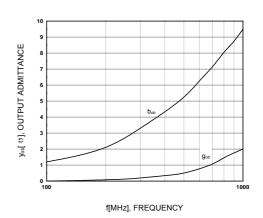
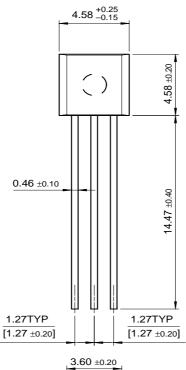


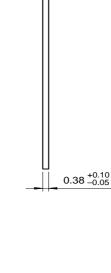
Figure 10. Rectangular Form

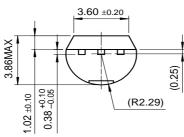
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TO-92







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